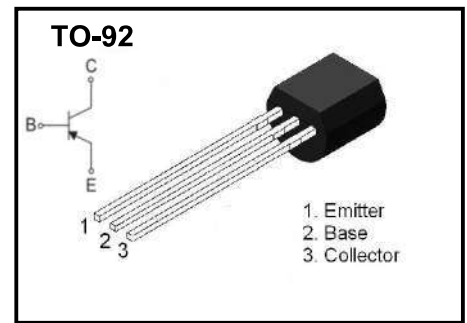


Plastic-Encapsulate Transistors
TRANSISTOR (PNP)

FEATURES

↓Power dissipation



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BC327 BC328 V_{CBO}	-50 -30	V
Collector-Emitter Voltage	BC327 BC328 V_{CEO}	-45 -25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-800	mA
Collector Power Dissipation	P_C	625	mW
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

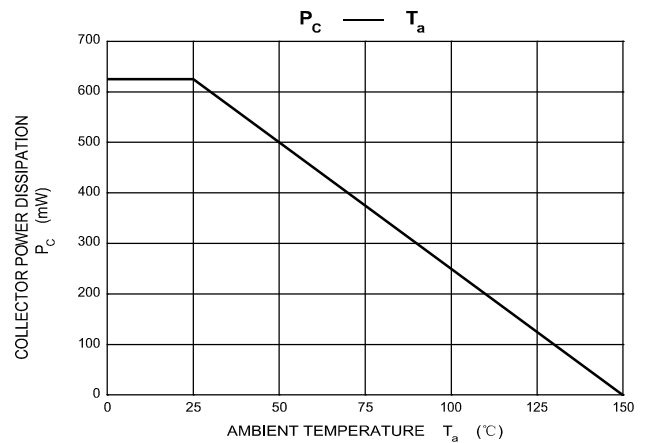
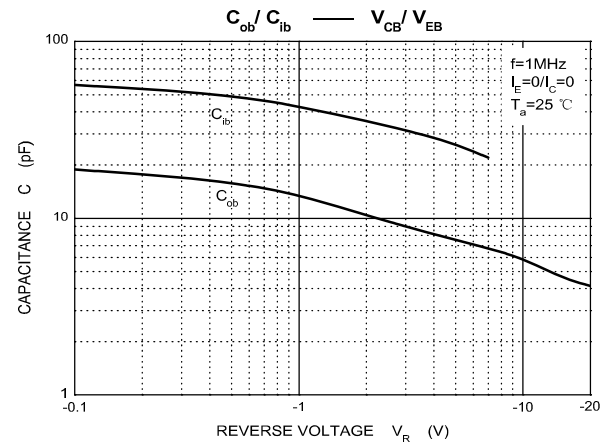
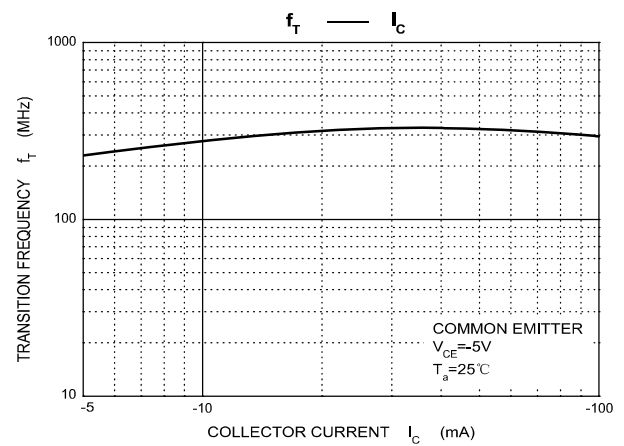
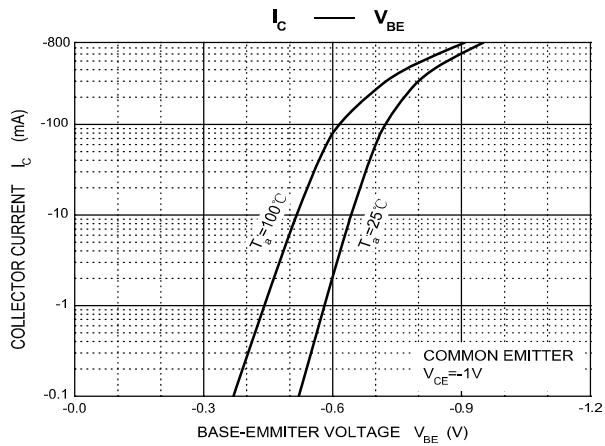
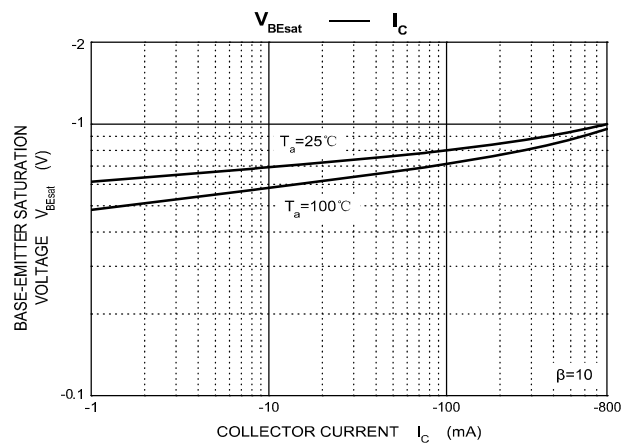
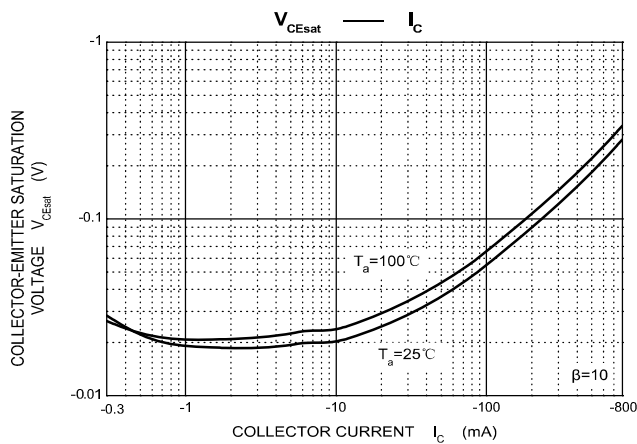
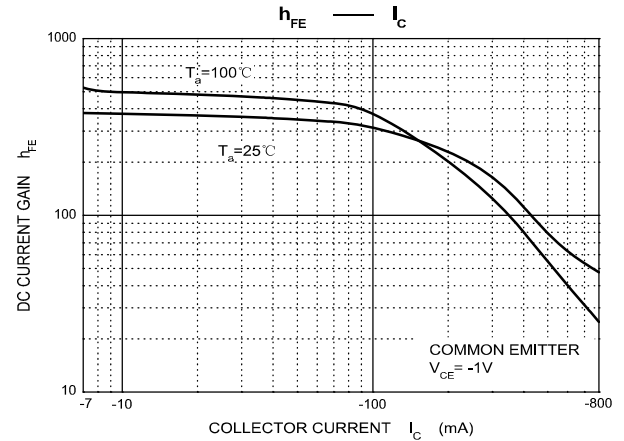
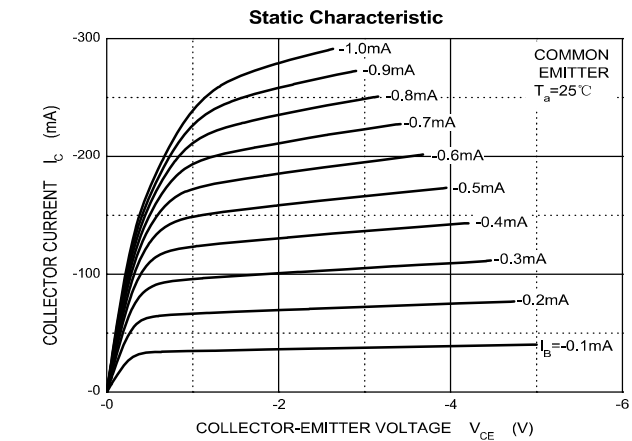
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BC327 BC328 V_{CBO}	$I_C = -100\mu A, I_E = 0$	-50 -30			V
Collector-emitter breakdown voltage	BC327 BC328 V_{CEO}	$I_C = -10mA, I_B = 0$	-45 -25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	BC327 BC328 I_{CBO}	$V_{CB} = -45V, I_E = 0$ $V_{CB} = -25V, I_E = 0$			-0.1 -0.1	μA
Collector cut-off current	BC327 BC328 I_{CEO}	$V_{CE} = -40V, I_B = 0$ $V_{CE} = -20V, I_B = 0$			-0.2 -0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	100		630	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -300mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.2	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -300mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 100MHz$	260			MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0$ $f = 1MHz$		12		pF

CLASSIFICATION OF h_{FE}

Rank	16	25	40
Range	100-250	160-400	250-630

Typical Characteristics



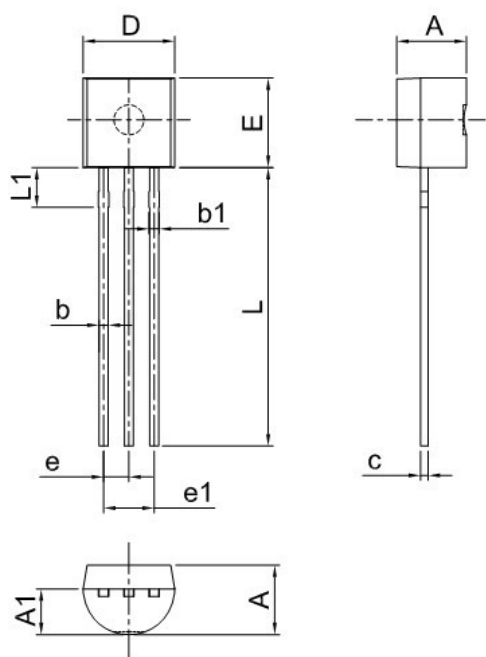
Ordering information

Package	Packing Description	Base Quantity
TO-92	Bulk	1000pcs/Bag
	Tape	2000pcs/Box

Package Dimensions

TO-92

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.70	0.130	0.146
A1	2.30	2.70	0.091	0.106
b	0.40	0.50	0.016	0.020
b1	0.50	0.70	0.020	0.028
c	0.35	0.45	0.014	0.018
D	4.45	4.70	0.175	0.185
E	4.40	4.65	0.173	0.183
e	1.17	1.37	0.046	0.054
e1	2.34	2.64	0.092	0.104
L	13.50	14.50	0.531	0.571
L1	1.80	2.20	0.071	0.087



Disclaimer

The information presented in this document is for reference only. GuangDong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <https://www.yfwdiode.com>, or consult YFW sales office for further assistance.